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July 2015

KA78LXXA / KA78L05AA

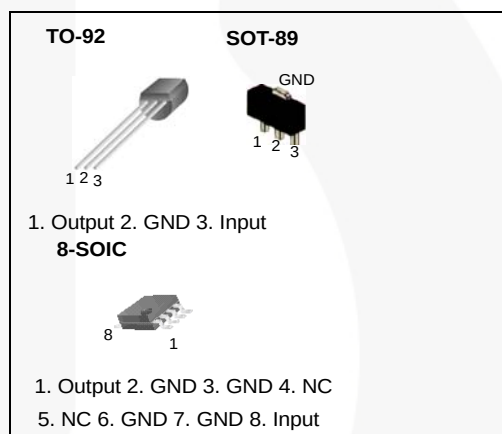
3-Terminal 0.1 A Positive Voltage Regulator

Features

- Maximum Output Current of 100 mA
- Output Voltage of 5 V, 6 V, 8 V, 9 V, 10 V, 12 V, 15 V and 18 V
- Thermal Overload Protection
- Short-Circuit Current Limiting
- Output Voltage Offered in $\pm 5\%$ Tolerance

Description

The KA78LXXA / KA78L05AA series of fixed-voltage, monolithic, integrated circuit, voltage regulators are suitable for applications that require supply current up to 100 mA.



Ordering Information

Product Number	Package	Packing Method	Output Voltage Tolerance	Operating Temperature
KA78L05AZTA	TO-92	Ammo	$\pm 5\%$	-40 to $+125$ °C
KA78L05AZBU		Bulk		
KA78L06AZTA		Ammo		
KA78L08AZTA		Ammo		
KA78L09AZTA		Ammo		
KA78L10AZTA		Ammo		
KA78L12AZTA		Ammo		
KA78L15AZTA		Ammo		
KA78L18AZTA		Ammo		
KA78L05AMTF	SOT-89	Tape & Reel	$\pm 5\%$	-40 to $+125$ °C
KA78L08AMTF		Tape & Reel		
KA78L12AMTF		Tape & Reel		
KA78L05ADTF	8-SOIC	Tape & Reel	$\pm 3\%$	0 to $+125$ °C
KA78L05AAZTA	TO-92	Ammo		

Block Diagram

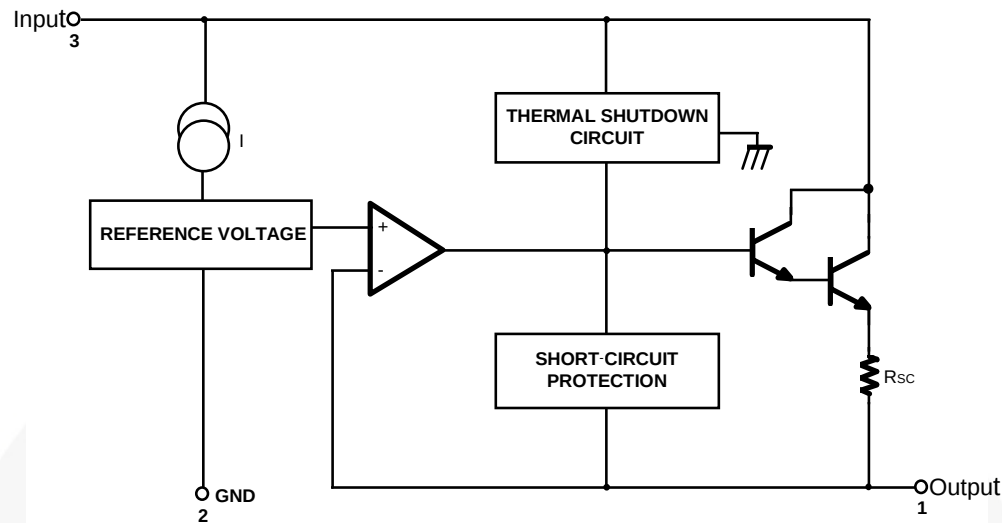


Figure 1. Block Diagram

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		Value	Unit
V_I	Input Voltage	$V_O = 5\text{ V to }8\text{ V}$	30	V
		$V_O = 12\text{ V to }18\text{ V}$	35	V
T_{OPR}	Operating Temperature Range	KA78LXXA	-40 to +125	$^\circ\text{C}$
		KA78L05AA	0 to +125	
$T_{\text{J(MAX)}}$	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-65 to +150	$^\circ\text{C}$
$R_{\theta\text{JC}}$	Thermal Resistance, Junction-Case	TO-92	50	$^\circ\text{C/W}$
$R_{\theta\text{JA}}$	Thermal Resistance, Junction-Air	TO-92	150	$^\circ\text{C/W}$
		SOT-89	225	$^\circ\text{C/W}$
		8-SOIC	160	$^\circ\text{C/W}$

Electrical Characteristics (KA78L05A)

$V_I = 10\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage		$T_J = 25^\circ\text{C}$	4.8	5.0	5.2	V
ΔV_O	Line Regulation ⁽¹⁾	$T_J = 25^\circ\text{C}$	$7\text{ V} \leq V_I \leq 20\text{ V}$		8	150	mV
			$8\text{ V} \leq V_I \leq 20\text{ V}$		6	100	mV
ΔV_O	Load Regulation ⁽¹⁾	$T_J = 25^\circ\text{C}$	$1\text{ mA} \leq I_O \leq 100\text{ mA}$		11	60	mV
			$1\text{ mA} \leq I_O \leq 40\text{ mA}$		5.0	30	mV
V_O	Output Voltage	$7\text{ V} \leq V_I \leq 20\text{ V}$	$1\text{ mA} \leq I_O \leq 40\text{ mA}$			5.25	V
		$7\text{ V} \leq V_I \leq V_{\text{MAX}}^{(2)}$	$1\text{ mA} \leq I_O \leq 70\text{ mA}$	4.75		5.25	V
I_Q	Quiescent Current		$T_J = 25^\circ\text{C}$		2.0	5.5	mA
ΔI_Q	Quiescent Current Change	With Line	$8\text{ V} \leq V_I \leq 20\text{ V}$			1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$			0.1	mA
V_N	Output Noise Voltage		$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		40		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O		$I_O = 5\text{ mA}$		-0.65		mV/ $^\circ\text{C}$
RR	Ripple Rejection		$f = 120\text{ Hz}$, $8\text{ V} \leq V_I \leq 18\text{ V}$, $T_J = 25^\circ\text{C}$	41	80		dB
V_D	Dropout Voltage		$T_J = 25^\circ\text{C}$		1.7		V

Notes:

1. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
2. Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L06A)

$V_I = 12\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage		$T_J = 25^\circ\text{C}$	5.75	6.00	6.25	V
ΔV_O	Line Regulation ⁽³⁾		$T_J = 25^\circ\text{C}$		64	175	mV
					54	125	mV
ΔV_O	Load Regulation ⁽³⁾		$T_J = 25^\circ\text{C}$		12.8	80.0	mV
					5.8	40.0	mV
V_O	Output Voltage		$8.5\text{ V} \leq V_I \leq 20\text{ V}$, $1\text{ mA} \leq I_O \leq 40\text{ mA}$			6.3	V
			$8.5\text{ V} \leq V_I \leq V_{\text{MAX}}^{(4)}$, $1\text{ mA} \leq I_O \leq 70\text{ mA}$	5.7		6.3	V
I_Q	Quiescent Current		$T_J = 25^\circ\text{C}$			5.5	mA
			$T_J = 125^\circ\text{C}$		3.9	6.0	mA
ΔI_Q	Quiescent Current Change	With Line	$9\text{ V} \leq V_I \leq 20\text{ V}$			1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$			0.1	mA
V_N	Output Noise Voltage		$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		40		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O		$I_O = 5\text{ mA}$		0.75		$\text{mV}/^\circ\text{C}$
RR	Ripple Rejection		$f = 120\text{ Hz}$, $10\text{ V} \leq V_I \leq 20\text{ V}$, $T_J = 25^\circ\text{C}$	40	46		dB
V_D	Dropout Voltage		$T_J = 25^\circ\text{C}$		1.7		V

Notes:

- The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
- Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L08A)

$V_I = 14\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage	$T_J = 25^\circ\text{C}$	7.7	8.0	8.3	V
ΔV_O	Line Regulation ⁽⁵⁾	$T_J = 25^\circ\text{C}$	$10.5\text{ V} \leq V_I \leq 23\text{ V}$	10	175	mV
			$11\text{ V} \leq V_I \leq 23\text{ V}$	8	125	mV
ΔV_O	Load Regulation ⁽⁵⁾	$T_J = 25^\circ\text{C}$	$1\text{ mA} \leq I_O \leq 100\text{ mA}$	15	80	mV
			$1\text{ mA} \leq I_O \leq 40\text{ mA}$	8	40	mV
V_O	Output Voltage	$10.5\text{ V} \leq V_I \leq 23\text{ V}$	$1\text{ mA} \leq I_O \leq 40\text{ mA}$	7.6	8.4	V
		$10.5\text{ V} \leq V_I \leq V_{\text{MAX}}^{(6)}$	$1\text{ mA} \leq I_O \leq 70\text{ mA}$	7.6	8.4	V
I_Q	Quiescent Current	$T_J = 25^\circ\text{C}$		2.0	5.5	mA
ΔI_Q	Quiescent Current Change	With Line	$11\text{ V} \leq V_I \leq 23\text{ V}$		1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$		0.1	mA
V_N	Output Noise Voltage	$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		60		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O	$I_O = 5\text{ mA}$		-0.8		$\text{mV}/^\circ\text{C}$
RR	Ripple Rejection	$f = 120\text{ Hz}$, $11\text{ V} \leq V_I \leq 21\text{ V}$, $T_J = 25^\circ\text{C}$	39	70		dB
V_D	Dropout Voltage	$T_J = 25^\circ\text{C}$		1.7		V

Notes:

- The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
- Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L09A)

$V_I = 15\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage	$T_J = 25^\circ\text{C}$	8.64	9.00	9.36	V
ΔV_O	Line Regulation ⁽⁷⁾	$T_J = 25^\circ\text{C}$	$11.5\text{ V} \leq V_I \leq 24\text{ V}$	90	200	mV
			$13\text{ V} \leq V_I \leq 24\text{ V}$	100	150	mV
ΔV_O	Load Regulation ⁽⁷⁾	$T_J = 25^\circ\text{C}$	$1\text{ mA} \leq I_O \leq 100\text{ mA}$	20	90	mV
			$1\text{ mA} \leq I_O \leq 40\text{ mA}$	10	45	mV
V_O	Output Voltage	$11.5\text{ V} \leq V_I \leq 24\text{ V}$	$1\text{ mA} \leq I_O \leq 40\text{ mA}$	8.55	9.45	V
		$11.5\text{ V} \leq V_I \leq V_{\text{MAX}}^{(8)}$	$1\text{ mA} \leq I_O \leq 70\text{ mA}$	8.55	9.45	V
I_Q	Quiescent Current	$T_J = 25^\circ\text{C}$		2.1	6.0	mA
ΔI_Q	Quiescent Current Change	With Line	$13\text{ V} \leq V_I \leq 24\text{ V}$		1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$		0.1	mA
V_N	Output Noise Voltage	$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		70		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O	$I_O = 5\text{ mA}$		-0.9		$\text{mV}/^\circ\text{C}$
RR	Ripple Rejection	$f = 120\text{ Hz}$, $12\text{ V} \leq V_I \leq 22\text{ V}$, $T_J = 25^\circ\text{C}$	38	44		dB
V_D	Dropout Voltage	$T_J = 25^\circ\text{C}$		1.7		V

Notes:

7. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
8. Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L10A)

$V_I = 16\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage		$T_J = 25^\circ\text{C}$	9.6	10.0	10.4	V
ΔV_O	Line Regulation ⁽⁹⁾		$T_J = 25^\circ\text{C}$ $12.5\text{ V} \leq V_I \leq 25\text{ V}$		100	220	mV
			$14\text{ V} \leq V_I \leq 25\text{ V}$		100	170	mV
ΔV_O	Load Regulation ⁽⁹⁾		$T_J = 25^\circ\text{C}$ $1\text{ mA} \leq I_O \leq 100\text{ mA}$		20	94	mV
			$1\text{ mA} \leq I_O \leq 70\text{ mA}$		10	47	mV
V_O	Output Voltage		$12.5\text{ V} \leq V_I \leq 25\text{ V}$, $1\text{ mA} \leq I_O \leq 40\text{ mA}$	9.5		10.5	V
			$12.5\text{ V} \leq V_I \leq V_{MAX}^{(10)}$, $1\text{ mA} \leq I_O \leq 70\text{ mA}$	9.5		10.5	
I_Q	Quiescent Current		$T_J = 25^\circ\text{C}$			6.0	mA
			$T_J = 125^\circ\text{C}$		4.2	6.5	
ΔI_Q	Quiescent Current Change	With Line	$12.5\text{ V} \leq V_I \leq 25\text{ V}$			1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$			0.1	mA
V_N	Output Noise Voltage		$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		74		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O		$I_O = 5\text{ mA}$		0.95		mV/ $^\circ\text{C}$
RR	Ripple Rejection		$f = 120\text{ Hz}$, $15\text{ V} \leq V_I \leq 25\text{ V}$, $T_J = 25^\circ\text{C}$	38	43		dB
V_D	Dropout Voltage		$T_J = 25^\circ\text{C}$		1.7		V

Notes:

9. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
10. Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L12A)

$V_I = 19\text{ V}$, $I_O = 40\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage		$T_J = 25^\circ\text{C}$	11.5	12.0	12.5	V
ΔV_O	Line Regulation ⁽¹¹⁾		$T_J = 25^\circ\text{C}$				
			$14.5\text{ V} \leq V_I \leq 27\text{ V}$		20	250	mV
			$16\text{ V} \leq V_I \leq 27\text{ V}$		15	200	mV
ΔV_O	Load Regulation ⁽¹¹⁾		$T_J = 25^\circ\text{C}$				
			$1\text{ mA} \leq I_O \leq 100\text{ mA}$		20	100	mV
			$1\text{ mA} \leq I_O \leq 40\text{ mA}$		10	50	mV
V_O	Output Voltage		$14.5\text{ V} \leq V_I \leq 27\text{ V}$				
			$1\text{ mA} \leq I_O \leq 40\text{ mA}$	11.4		12.6	V
			$14.5\text{ V} \leq V_I \leq V_{\text{MAX}}^{(12)}$				
			$1\text{ mA} \leq I_O \leq 70\text{ mA}$	11.4		12.6	V
I_Q	Quiescent Current		$T_J = 25^\circ\text{C}$		2.1	6.0	mA
ΔI_Q	Quiescent Current Change	With Line	$16\text{ V} \leq V_I \leq 27\text{ V}$			1.5	mA
ΔI_Q		With Load	$1\text{ mA} \leq I_O \leq 40\text{ mA}$			0.1	mA
V_N	Output Noise Voltage		$T_A = 25^\circ\text{C}$, $10\text{ Hz} \leq f \leq 100\text{ kHz}$		80		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O		$I_O = 5\text{ mA}$		-1.0		$\text{mV}/^\circ\text{C}$
RR	Ripple Rejection		$f = 120\text{ Hz}$, $15\text{ V} \leq V_I \leq 25\text{ V}$, $T_J = 25^\circ\text{C}$	37	65		dB
V_D	Dropout Voltage		$T_J = 25^\circ\text{C}$		1.7		V

Notes:

11. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

12. Power dissipation: $P_D \leq 0.75\text{ W}$.

Electrical Characteristics (KA78L15A)

$V_I = 23 \text{ V}$, $I_O = 40 \text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33 \mu\text{F}$, $C_O = 0.1 \mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage		$T_J = 25^\circ\text{C}$	14.4	15.0	15.6	V
ΔV_O	Line Regulation ⁽¹³⁾		$T_J = 25^\circ\text{C}$				
			$17.5 \text{ V} \leq V_I \leq 30 \text{ V}$		25	300	mV
			$20 \text{ V} \leq V_I \leq 30 \text{ V}$		20	250	mV
ΔV_O	Load Regulation ⁽¹³⁾		$T_J = 25^\circ\text{C}$				
			$1 \text{ mA} \leq I_O \leq 100 \text{ mA}$		25	150	mV
			$1 \text{ mA} \leq I_O \leq 40 \text{ mA}$		12	75	mV
V_O	Output Voltage		$17.5 \text{ V} \leq V_I \leq 30 \text{ V}$	$1 \text{ mA} \leq I_O \leq 40 \text{ mA}$	14.25		15.75 V
			$17.5 \text{ V} \leq V_I \leq V_{\text{MAX}}^{(14)}$	$1 \text{ mA} \leq I_O \leq 70 \text{ mA}$	14.25		15.75 V
I_Q	Quiescent Current		$T_J = 25^\circ\text{C}$		2.1	6.0	mA
ΔI_Q	Quiescent Current Change	With Line	$20 \text{ V} \leq V_I \leq 30 \text{ V}$			1.5	mA
ΔI_Q		With Load	$1 \text{ mA} \leq I_O \leq 40 \text{ mA}$			0.1	mA
V_N	Output Noise Voltage		$T_A = 25^\circ\text{C}$, $10 \text{ Hz} \leq f \leq 100 \text{ kHz}$		90		$\mu\text{V}/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O		$I_O = 5 \text{ mA}$		-1.3		mV/ $^\circ\text{C}$
RR	Ripple Rejection		$f = 120 \text{ Hz}$, $18.5 \text{ V} \leq V_I \leq 28.5 \text{ V}$, $T_J = 25^\circ\text{C}$	34	60		dB
V_D	Dropout Voltage		$T_J = 25^\circ\text{C}$		1.7		V

Notes:

13. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

14. Power dissipation: $P_D \leq 0.75 \text{ W}$.

Electrical Characteristics (KA78L18A)

$V_I = 27V$, $I_O = 40mA$, $-40^{\circ}C \leq T_J \leq 125^{\circ}C$, $C_I = 0.33 \mu F$, $C_O = 0.1 \mu F$, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_O	Output Voltage	$T_J = 25^{\circ}C$	17.3	18.0	18.7	V
ΔV_O	Line Regulation ⁽¹⁵⁾	$T_J = 25^{\circ}C$	$21 V \leq V_I \leq 33 V$	145	300	mV
			$22 V \leq V_I \leq 33 V$	135	250	mV
ΔV_O	Load Regulation ⁽¹⁵⁾	$T_J = 25^{\circ}C$	$1 mA \leq I_O \leq 100 mA$	30	170	mV
			$1 mA \leq I_O \leq 40 mA$	15	85	mV
V_O	Output Voltage	$21 V \leq V_I \leq 33 V$	$1 mA \leq I_O \leq 40 mA$	17.1	18.9	V
		$21V \leq V_I \leq V_{MAX}^{(16)}$	$1 mA \leq I_O \leq 70 mA$	17.1	18.9	V
I_Q	Quiescent Current	$T_J = 25^{\circ}C$		2.2	6.0	mA
ΔI_Q	Quiescent Current Change	With Line	$21 V \leq V_I \leq 33 V$		1.5	mA
ΔI_Q		With Load	$1 mA \leq I_O \leq 40 mA$		0.1	mA
V_N	Output Noise Voltage	$T_A = 25^{\circ}C$, $10 Hz \leq f \leq 100 kHz$		150		$\mu V/V_O$
$\Delta V_O/\Delta T$	Temperature Coefficient of V_O	$I_O = 5 mA$		-1.8		mV/ $^{\circ}C$
RR	Ripple Rejection	$f = 120 Hz$, $23 V \leq V_I \leq 33V$, $T_J = 25^{\circ}C$	34	48		dB
V_D	Dropout Voltage	$T_J = 25^{\circ}C$		1.7		V

Notes:

15. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

16. Power dissipation: $P_D \leq 0.75 W$.

Electrical Characteristics (KA78L05AA)

$V_I = 10\text{ V}$, $I_O = 40\text{ mA}$, $0^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$, $C_I = 0.33\text{ }\mu\text{F}$, $C_O = 0.1\text{ }\mu\text{F}$, unless otherwise specified.

Symbol	Parameter		Conditions		Min.	Typ.	Max.	Unit
V _O	Output Voltage		T _J = 25°C		4.9	5.0	5.1	V
ΔV _O	Line Regulation ⁽¹⁷⁾		T _J = 25°C	7 V ≤ V _I ≤ 20 V		8	150	mV
				8 V ≤ V _I ≤ 20 V		6	100	mV
ΔV _O	Load Regulation ⁽¹⁷⁾		T _J = 25°C	1 mA ≤ I _O ≤ 100 mA		11	50	mV
				1 mA ≤ I _O ≤ 40 mA		5.0	25	mV
V _O	Output Voltage		7 V ≤ V _I ≤ 20 V	1 mA ≤ I _O ≤ 40 mA			5.15	V
			7 V ≤ V _I ≤ V _{MAX} ⁽¹⁸⁾	1 mA ≤ I _O ≤ 70 mA	4.85		5.15	V
I _Q	Quiescent Current		T _J = 25°C			2.0	5.5	mA
ΔI _Q	Quiescent Current Change	With Line	8 V ≤ V _I ≤ 20 V				1.5	mA
ΔI _Q		With Load	1 mA ≤ I _O ≤ 40 mA				0.1	mA
V _N	Output Noise Voltage		T _A = 25°C, 10 Hz ≤ f ≤ 100 kHz			40		μV/V _O
ΔV _O /ΔT	Temperature Coefficient of V _O		I _O = 5 mA			-0.65		mV/°C
RR	Ripple Rejection		f = 120 Hz, 8 V ≤ V _I ≤ 18 V, T _J = 25°C		41	80		dB
V _D	Dropout Voltage		T _J = 25°C			1.7		V

Notes:

17. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

18. Power dissipation: $P_D \leq 0.75\text{ W}$.

Typical Application

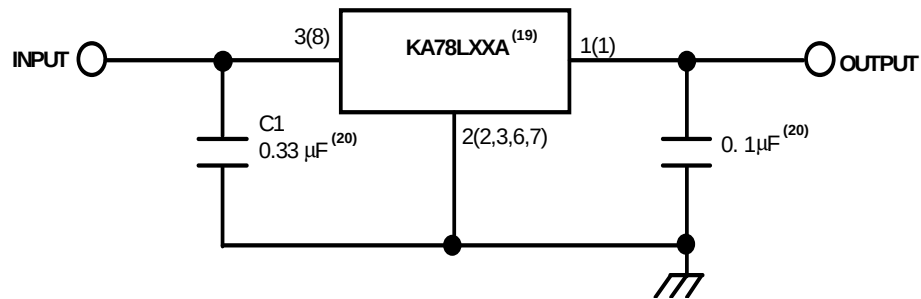
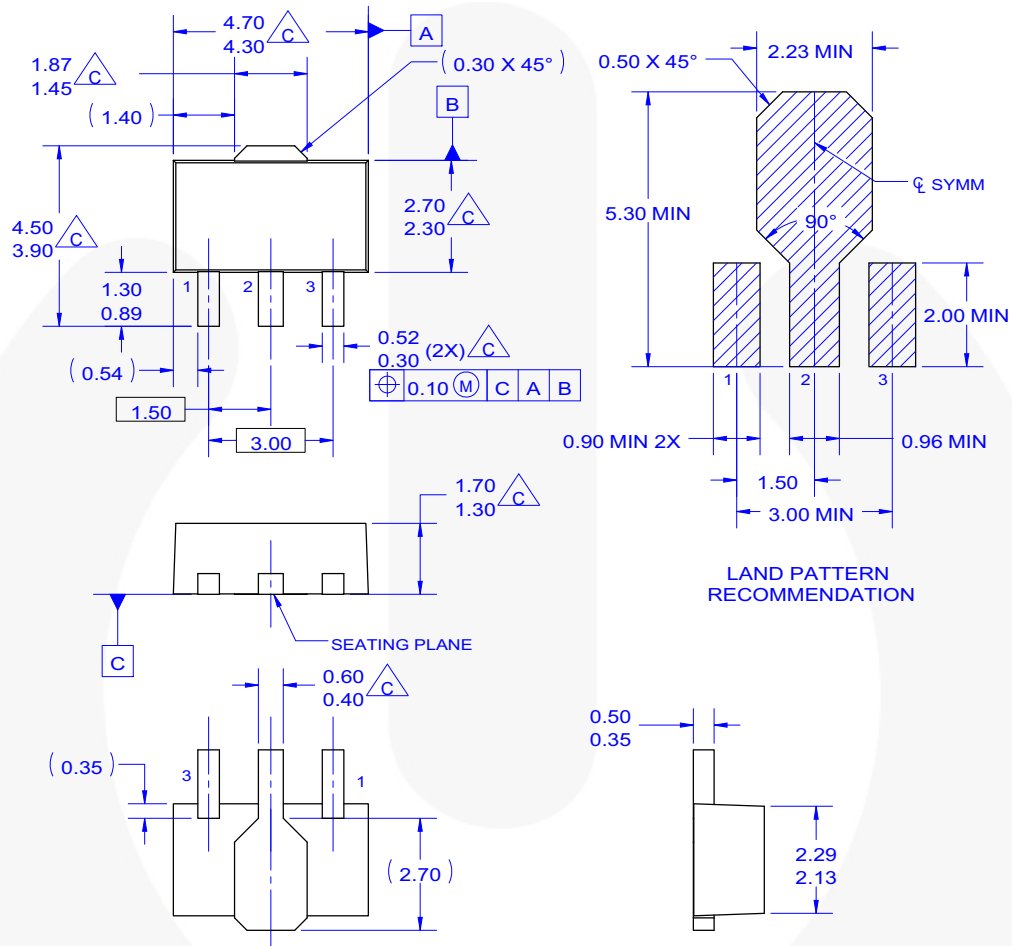


Figure 2. Typical Application

Notes:

- 19. To specify an output voltage, substitute voltage value for "XX".
- 20. Bypass capacitors are recommended for optimum stability and transient response and should be located as close as possible to the regulator.

Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

A. REFERENCE TO JEDEC TO-243 VARIATION AA.
B. ALL DIMENSIONS ARE IN MILLIMETERS.

C. DOES NOT COMPLY JEDEC STANDARD VALUE.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS,
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E. DIMENSION AND TOLERANCE AS PER ASME
Y14.5-1994.
F. DRAWING FILE NAME: MA03CREV3

Figure 3. 3-LEAD, SOT-89, JEDEC TO-243, OPTION AA

Physical Dimensions (Continued)

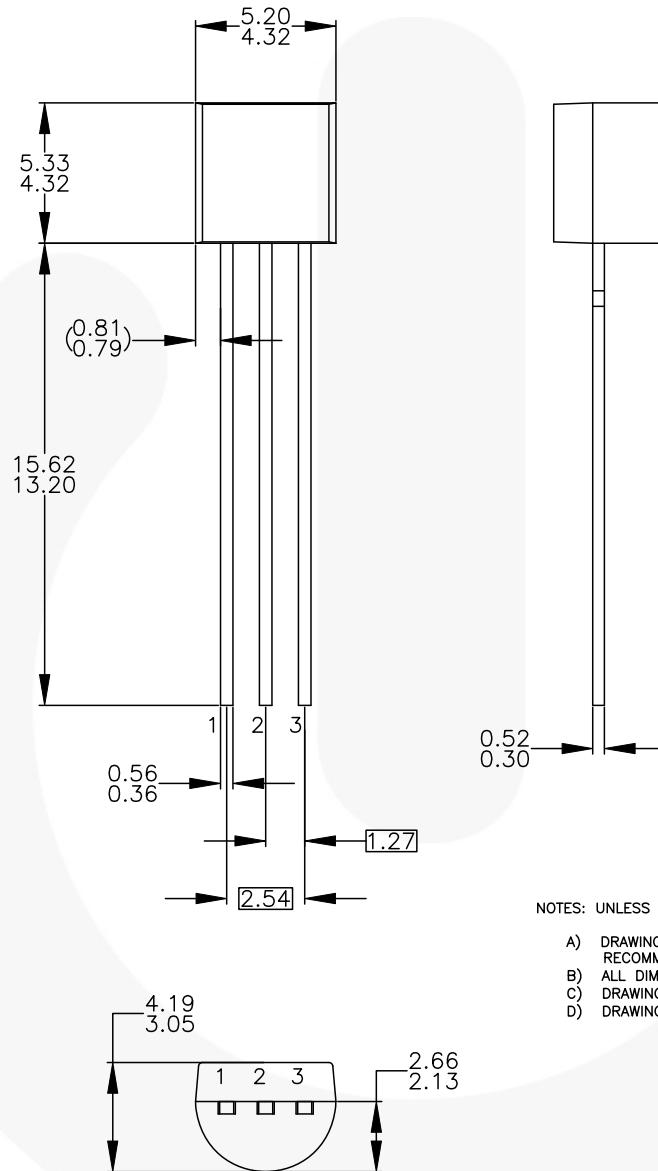
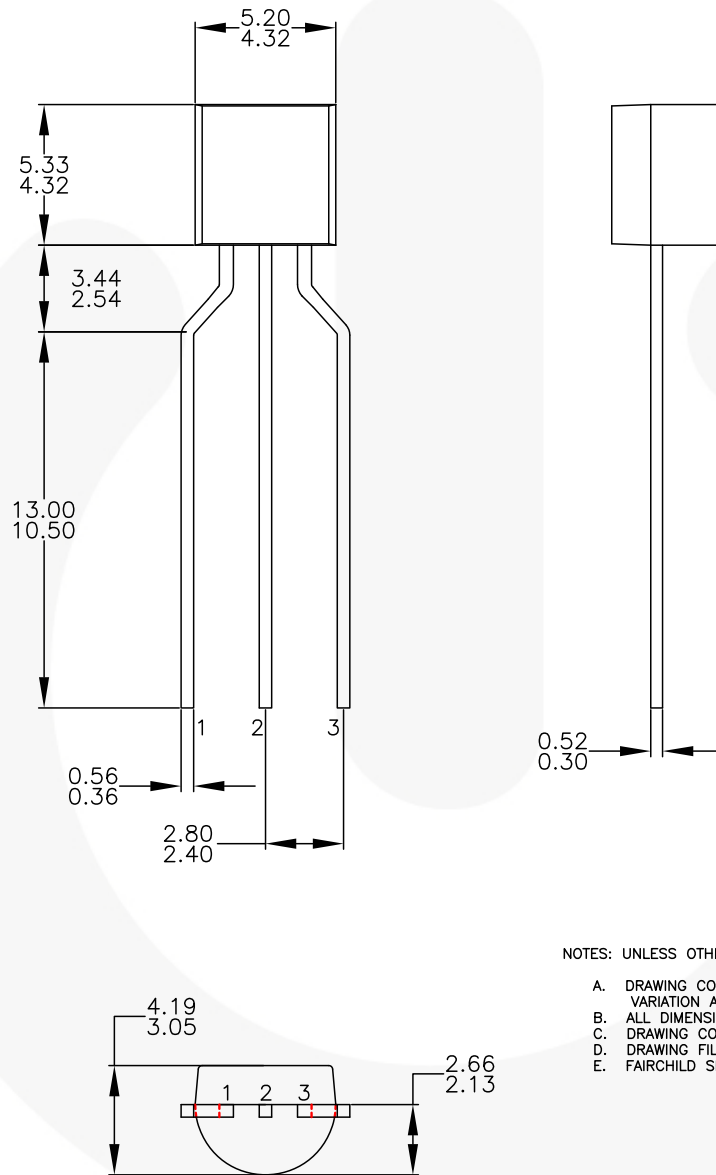


Figure 4. 3-LEAD, TO-92, JEDEC TO-92 COMPLIANT STRAIGHT LEAD CONFIGURATION, BULK TYPE

Physical Dimensions (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
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- E. FAIRCHILD SEMICONDUCTOR.

Figure 5. 3-LEAD, TO-92, MOLDED 0.200 IN LINE SPACING LEAD FORM, AMMO TYPE

Physical Dimensions (Continued)

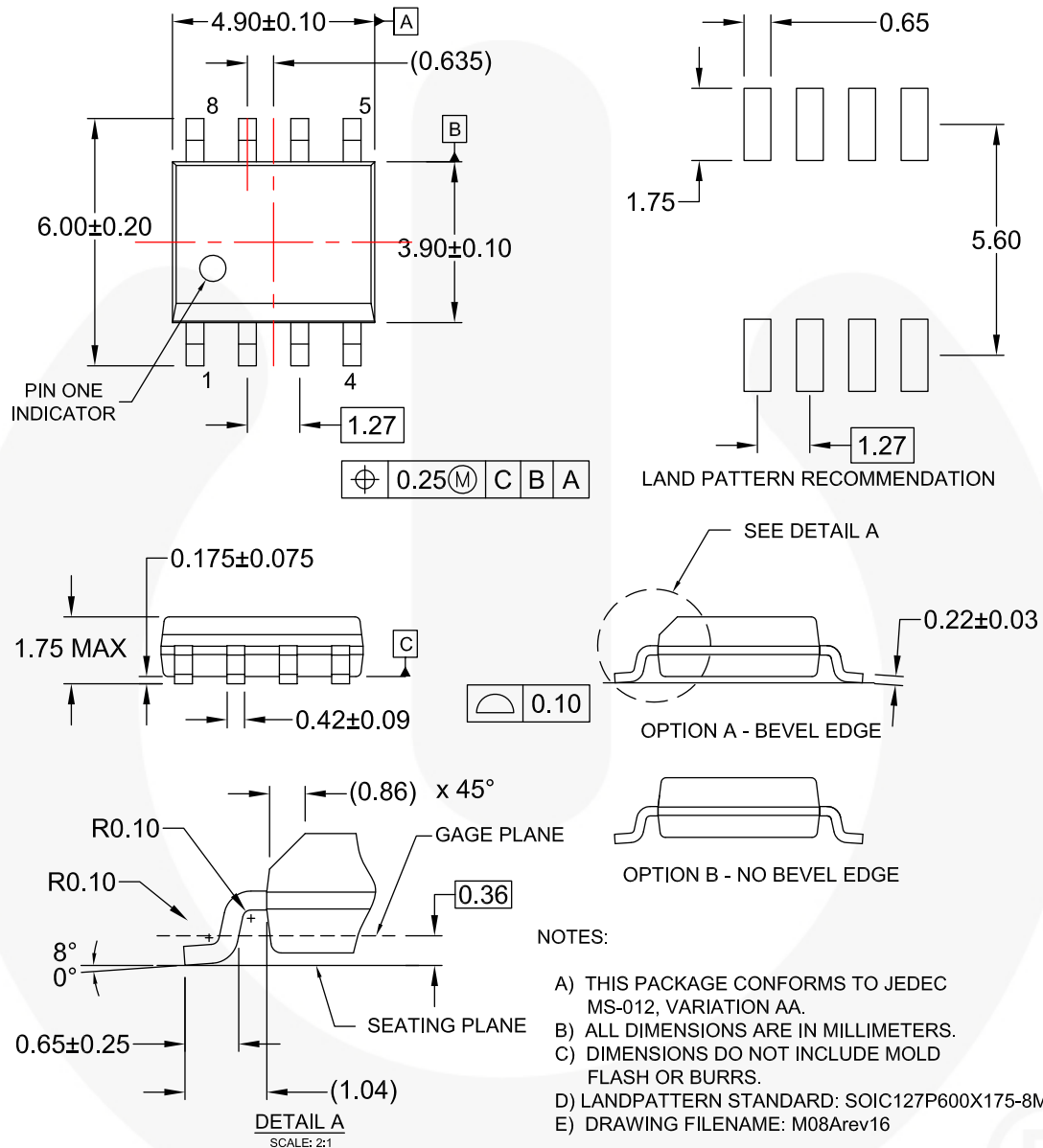


Figure 6. 8-LEAD, SOIC, JEDEC MS-012, 0.150" NARROW BODY



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